

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6712	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:06
L2	143	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:07
L3	0	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and temperature and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:09
L4	0	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11
L5	14	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and sensor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11
L6	5	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:26
L7	1	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor) and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:28

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L8	0	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor) and GaAs	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:34
L9	37	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:35
L10	3	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite and thermocouple	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:41
L11	3	(substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite and thermocouple and laser	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:41
S1	369	(oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:05
S2	326	(oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:22
S3	54	(oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support) and time	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:23

## EAST Search History

S4	7	(oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support) and time and condensat\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:24
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